(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
4 January 2007 (04.01.2007)

PCT

(10) International Publication Number
WO 2007/001722 A1

(51) International Patent Classification:
H01L 21/762 (2006.01)

(21) International Application Number:
PCT/US2006/020877

(22) International Filing Date: 24 May 2006 (24.05.2006)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/168,861 28 June 2005 (28.06.2005) US

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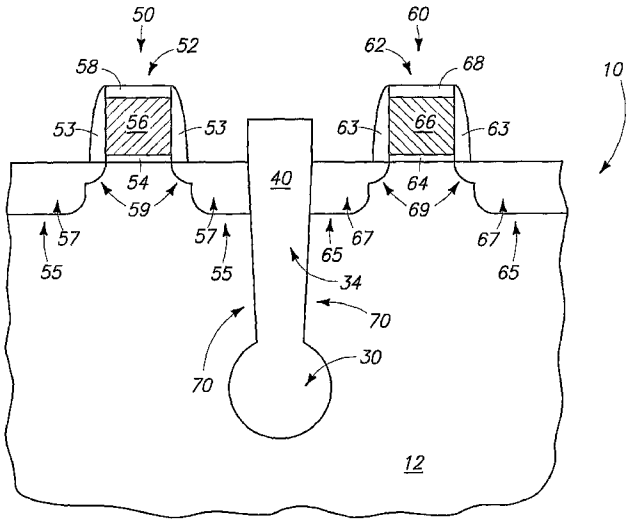
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *with amended claims*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR PROCESSING METHODS, AND SEMICONDUCTOR CONSTRUCTIONS



(57) Abstract: The invention includes methods of forming isolation regions. An opening can be formed to extend into a semiconductor material, and an upper periphery of the opening can be protected with a liner while a lower periphery is unlined. The unlined portion can then be etched to form a widened region of the opening. Subsequently, the opening can be filled with insulative material to form an isolation region. Transistor devices can then be formed on opposing sides of the isolation region, and electrically isolated from one another with the isolation region. The invention also includes semiconductor constructions containing an electrically insulative isolation structure extending into a semiconductor material, with the structure having a bulbous bottom region and a stem region extending upwardly from the bottom region to a surface of the semiconductor material.

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